

ABSTRACT

There is provided a bonding wire for semiconductor devices that exhibits a favorable bondability even when
5 being applied to wedge bonding at the room temperature, and also achieves an excellent bond reliability. The bonding wire includes a core material of Cu or Cu alloy (hereinafter referred to as a "Cu core material"), and a coating containing a noble metal formed on a surface of the
10 Cu core material. A concentration of Cu at a surface of the wire is 30 to 80 at%.

[No figure]